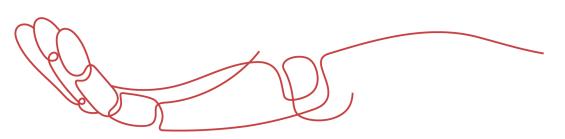




# **PRODUCT DATA SHEET**



To learn more about JGSEMI, please visit our website at







Datasheet

Samples

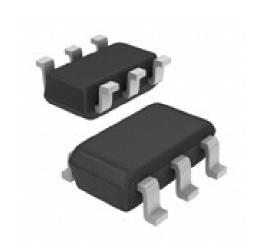
Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.



**ESD Protection Diode Array** 

#### **Features**

- 300Watts peak pulse power (tp =  $8/20\mu$ s)
- SOT23-6 package
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.8pF typ. IO to IO)
- Protection one data/power line to:
- IEC 61000-4-2  $\pm$ 30kV contact  $\pm$ 30kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 16A (8/20μs)



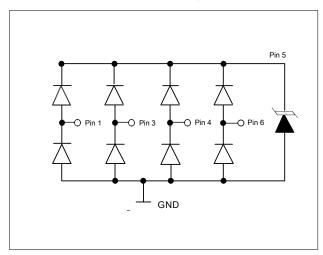
## **Applications**

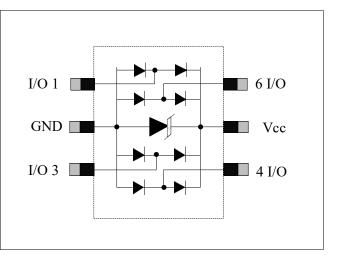
- Ethernet
- Digital Visual Interface (DVI)
- USB2.0
- Notebook and PC Computers

#### **Mechanical Data**

- SOT23-6 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

## Schematic & PIN Configuration







**Absolute Maximum Rating** 

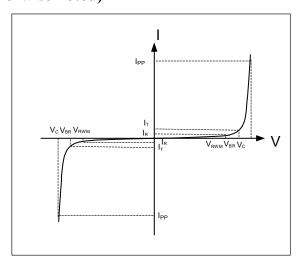
Rating	Symbol	Value	Units	
Peak Pulse Power (t <sub>p</sub> =8/20μs)	P <sub>PP</sub>	300	Watts	
Peak Pulse Current ( t <sub>p</sub> =8/20μs ) (note1)	$I_{pp}$	16	A	
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	$V_{ESD}$	30 30	kV	
Lead Soldering Temperature	$T_{L}$	260(10seconds)	$^{\circ}$	
Junction Temperature	$T_{\mathrm{J}}$	-55 to + 125	$^{\circ}$	
Storage Temperature	$T_{ m stg}$	-55 to + 125	$^{\circ}$	

#### **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	6			V
Reverse Leakage Current	$I_R$	V <sub>RWM</sub> =5V,T=25°C			1.0	uA
Peak Pulse Current	$I_{PP}$	tp =8/20μs			16	A
Clamping Voltage	$V_{\rm C}$	$I_{PP}=1A, t_p=8/20 \mu s$		8.5		V
Clamping Voltage	$V_{\rm C}$	$I_{PP}=16A, t_p=8/20 \mu s$		20		V
Junction Capacitance	$C_{j}$	$V_R = 0V$ , $f = 1MHz$ IO to IO		0.8	1.4	pF
		$V_R = 0V, f = 1MHz$ IO to GND		1.6	2.2	

## Electrical Parameters (TA = 25°C unless otherwise noted)

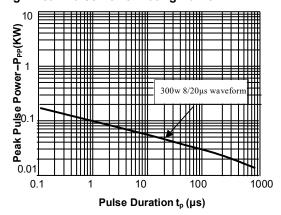
Symbol	Parameter
$\mathbf{I}_{\mathrm{PP}}$	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ IPP
V <sub>RWM</sub>	Working Peak Reverse Voltage
Ir	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
$ m V_{BR}$	Breakdown Voltage @ IT
Iт	Test Current





## **Typical Characteristic Curves**

Fig.1 Peak Pulse Power Rating Curve



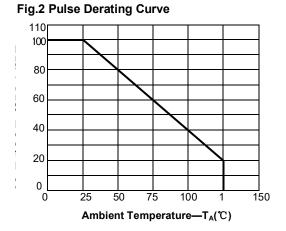


Fig.3 Pulse Waveform-8/20µs

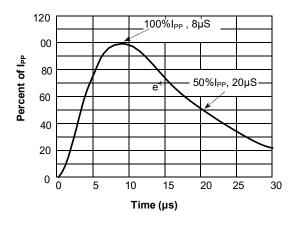
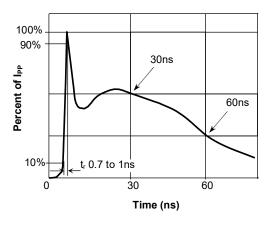


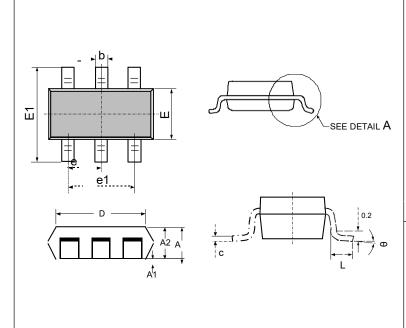
Fig.4 Pulse Waveform-ESD(IEC61000-4-2)





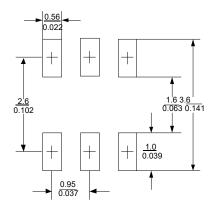
## **Outline Drawing – SOT23-6**

#### **PACKAGE OUTLINE**



DIMENSIONS						
SYMBOL	INCHES		MILLIMETER			
	MIN	MAX	MIN	MAX		
Α	0.041	0.049	1.050	1.250		
A1	0.000	0.004	0.000	0.100		
A2	0.041	0.045	1.050	1.150		
D	0.111	0.119	2.820	3.020		
E	0.059	0.067	1.500	1.700		
E1	0.104	0.116	2.650	2.950		
b	0.012	0.020	0.300	0.500		
е	0.037(BSC)		0.950(BSC)			
e1	0.071	0.079	1.800	2.000		
L	0.012	0.024	0.300	0.600		
θ	0°	8°	0°	8°		





Notes
1. This land pattern is for reference purposes only consult your manufacturing group to ensure your company's manufacturing guidelines are met.



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